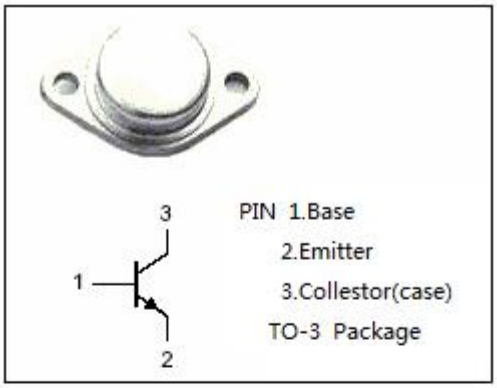
isc Silicon NPN Power Transistor — BUY18S

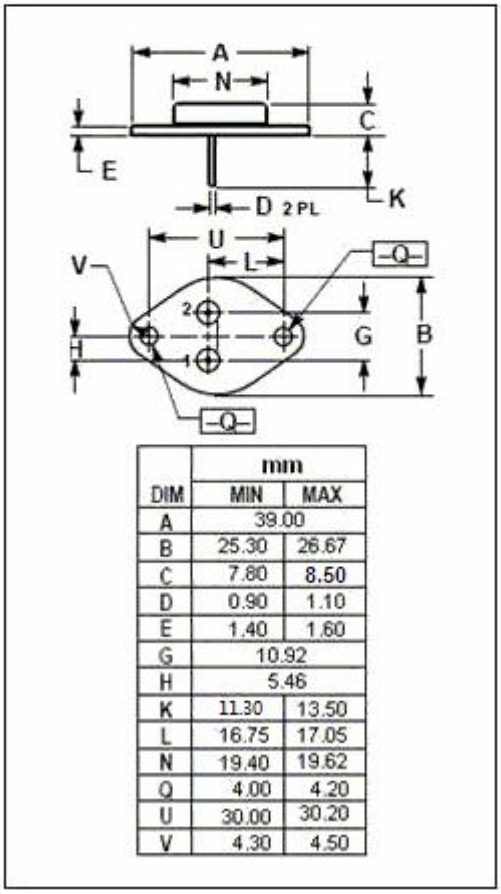
DESCRIPTION

- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= 200V(MIN)
- Low Collector Saturation Voltage-
  : $V_{CE(sat)}$= 1.0V@ I_C= 5A
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for use switching and general purpose applications.





DIM	mm MIN	MAX
A	39.00	
B	25.30	26.67
C	7.80	8.50
D	0.90	1.10
E	1.40	1.60
G	10.92	
H	5.46	
K	11.30	13.50
L	16.75	17.05
N	19.40	19.62
Q	4.00	4.20
U	30.00	30.20
V	4.30	4.50

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	400	V
V_{CEO}	Collector-Emitter Voltage	200	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	7	A
P_C	Collector Power Dissipation @T_C＜75℃	50	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	2.08	℃/W

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= 50mA; I_B= 0	200			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= 1mA; I_E= 0	400			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1m A; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 0.5A			1.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 5A; I_B= 0.5A			1.2	V
I_{CBO}	Collector Cutoff Current	V_{CB}=400V; I_E= 0			10	μA
h_{FE}	DC Current Gain	I_C= 1A ; V_{CE}= 5V	20			
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A; V_{CE}= 5V		50		MHz